

Atty. Docket No. OPP030889US
Serial No: 10/676,645

Amendments to the Specification

Please replace paragraph [0010], beginning at page 4, line 12, with the following replacement paragraph:

[0010] Silicon nitride or silicon oxy-nitride may be used as a protection layer 6. A barrier metal layer 10 made of Ti, Ta, TiN, or TaN is formed along inner walls of a via 100. The barrier metal layer 10 prevents the copper line 3 from permeating an insulation layer 2. The copper line 3 may be formed on the barrier metal layer 10. The barrier metal layer 10 is preferably formed to a thickness of between 200 Å and 800 Å.

Please replace paragraph [0012], beginning at page 5, line 1, with the following replacement paragraph:

[0012] Before depositing the copper layer 3, a barrier metal layer 10 formed of a material such as Ta, Ti, TaN, and TiN is formed on the insulation layer 2. The barrier metal layer 10 is formed to a thickness between 200 and 800 Å, preferably 500 Å. The barrier metal layer 10 prevents the copper layer 3 from permeating the insulation layer 2.

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